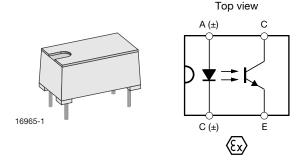


Vishay Semiconductors

Optocoupler, Phototransistor Output, ATEX Certified



DESCRIPTION

The CNY65Exi consists of a phototransistor optically coupled to an infrared-emitting diode in a 4 pin plastic package. The components are mounted opposite one another, with a distance between input and output of > 3.0 mm; meeting the highest of safety requirements.

The CNY65Exi is ATEX certificated for explosive atmospheres according to the European Guide line 94/9/EG.

AGENCY APPROVALS

• ATEX (Ex): PTB 03 ATEX 2033 U EN 60079-0:2012 EN 60079-11:2012 EN 60079-26:2007

FEATURES

 ATEX certificate: PTB 03 ATEX 2033 U <u>www.vishay.com/doc?85361</u>



Suitable for intrinsic safe circuits for gas and dust



· Gas safety provision: II (1) G (EX ia) IIC

• Dust safety provision: II (1) D (EX ia) IIIC

RoHS COMPLIAN

- Conforms to EN60079-0:2012
- Qualified for continuously, longterm, or frequently dangerous explosive environments, zone 0
- Isolation voltage (V_{ISO}) of 11 600 V_{peak} for 1 minute
- Distance from emitter to detector through insulation ≥ 3 mm
- CTR from 50 % to 300 %
- Very low coupling capacity (C_K)
 - 0.3 pF superior noise immunity between input and output pins
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Electronics used in potentially explosive gas and dust environments
 - Safety related process automation and instrumentation
 - Natural gas metering and flow measurement
 - Power and motor switching
 - Power supplies, metering, and data acquisition
 - Lighting and signaling
 - Petrol and grain transport and storage

ORDERING INFORMATION							
C N Y PART NUMBER	6 5 X CTR BIN	E x i PACKAGE OPTION		DIP-4			
AGENCY CERTIFIED/PACKAGE	CTR (%)						
ATEX	50 to 300		100 to 200				
DIP-4, HV, high isolation distance	CNY65Exi		CNY65BExi				



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PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
INPUT	<u> </u>				
Reverse voltage		V _R	5	V	
Forward current		I _F	75	mA	
Forward surge current	t _p ≤ 10 μs	I _{FSM}	1.5	Α	
Power dissipation		P _{diss}	120	mW	
Junction temperature		Tj	100	°C	
OUTPUT					
Collector emitter voltage		V_{CEO}	32	V	
Emitter collector voltage		V _{ECO}	7	V	
Collector current		I _C	50	mA	
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _{CM}	100	mA	
Power dissipation		P _{diss}	130	mW	
Junction temperature		T _j	100	°C	
COUPLER					
DC isolation test voltage	t = 1 min	V _{ISO}	11.6	kV	
Total power dissipation		P _{tot}	250	mW	
Ambient temperature range		T _{amb}	-55 to +85	°C	
Storage temperature range		T _{stg}	-55 to +100	°C	
Soldering temperature	2 mm from case, t ≤ 10 s	T _{sld}	260	°C	

Note

• Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT								
Forward voltage	I _F = 50 mA	V_{F}		1.25	1.6	V		
OUTPUT								
Collector emitter voltage	I _C = 1 mA	V_{CEO}	32			V		
Emitter collector voltage	I _E = 100 μA	V _{ECO}	7			V		
Collector dark current	$V_{CE} = 20 \text{ V}, I_f = 0, E = 0$	I _{CEO}			200	nA		
COUPLER								
DC isolation test voltage	t = 1 min	V _{ISO} (1)	11.6			kV		
Isolation resistance	V _{IO} = 1 kV, 40 % relative humidity	R _{IO} (1)		10 ¹²		Ω		
Collector saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V _{CEsat}			0.3	V		
Cut-off frequency	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA},$ $R_L = 100 \Omega$	f _c	110			kHz		
Coupling capacitance	f = 1 MHz	C _k		0.3		pF		

Notes

- Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.
- (1) Related to standard climate 23/50 DIN 50014.

CURRENT TRANSFER RATIO (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I _C /I _F	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}$	CNY65Exi	CTR	50	100	300	%
		CNY65BExi	CTR	100		200	%



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SWITCHING CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Delay time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$, (see figure 1)	t _d		2.6		μs	
Rise time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$, (see figure 1)	t _r		2.4		μs	
Fall time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$, (see figure 1)	t _f		2.4		μs	
Storage time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$, (see figure 1)	ts		0.3		μs	
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega, \text{ (see figure 1)}$	t _{on}		5		μs	
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$, (see figure 1)	t _{off}		3		μs	
Turn-on time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega, \text{ (see figure 2)}$	t _{on}		25		μs	
Turn-off time	$V_S = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 1 \text{ k}\Omega$, (see figure 2)	t _{off}		42.5		μs	

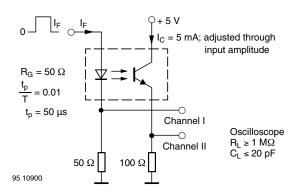


Fig. 1 - Test Circuit, Non-Saturated Operation

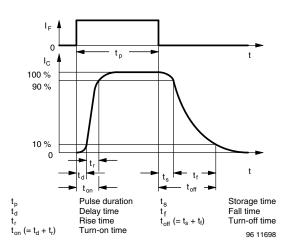


Fig. 3 - Switching Times

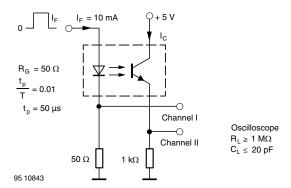


Fig. 2 - Test Circuit, Saturated Operation



TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

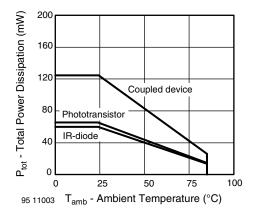


Fig. 4 - Total Power Dissipation vs. Ambient Temperature

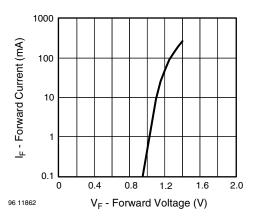


Fig. 5 - Forward Current vs. Forward Voltage

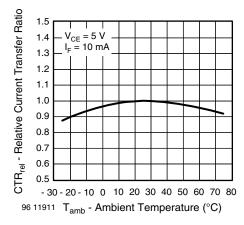


Fig. 6 - Relative Current Transfer Ratio vs.
Ambient Temperature

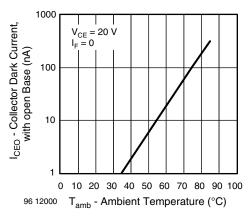


Fig. 7 - Collector Dark Current vs. Ambient Temperature

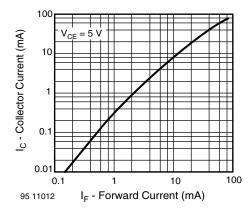


Fig. 8 - Collector Current vs. Forward Current

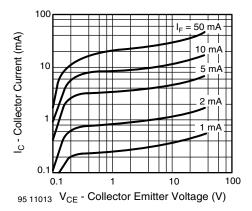


Fig. 9 - Collector Current vs. Collector Emitter Voltage



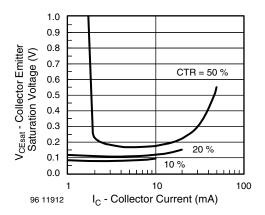


Fig. 10 - Collector Emitter Saturation Voltage vs. Collector Current

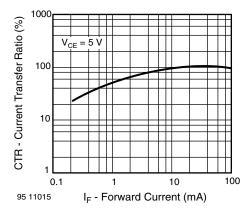


Fig. 11 - Current Transfer Ratio vs. Forward Current

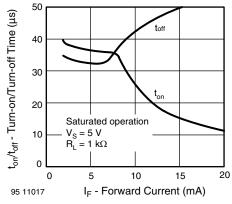


Fig. 12 - Turn-on/Turn-off Time vs. Forward Current

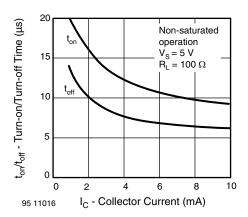
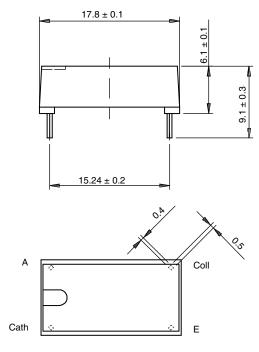


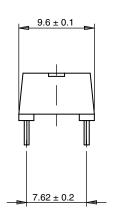
Fig. 13 - Turn-on/Turn-off Time vs. Collector Current



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PACKAGE DIMENSIONS in millimeters







Weight: ca. 1.40 g Creepage distance: > 14 mm Air path: > 14 mm after mounting on PC board

Drawing-No.: 6.544-5036.01-1

Issue: 2; 10.11.98

14763

PACKAGE MARKING (example of CNY65BExi)



HANDLING AND STORAGE CONDITIONS

ESD level: HBM class 2



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